

CORRECTION

[View Article Online](#)  
[View Journal](#) | [View Issue](#)



Cite this: *J. Mater. Chem. A*, 2015, **3**, 916

DOI: 10.1039/c4ta90219j

[www.rsc.org/MaterialsA](http://www.rsc.org/MaterialsA)

## Correction: Plasma enhanced atomic layer deposition of $\text{Ga}_2\text{O}_3$ thin films

Ranjith K. Ramachandran,<sup>a</sup> Jolien Dendooven,<sup>a</sup> Jonas Botterman,<sup>b</sup> Sreeprasanth Pulinthanathu Sree,<sup>c</sup> Dirk Poelman,<sup>b</sup> Johan A. Martens,<sup>c</sup> Hilde Poelman<sup>d</sup> and Christophe Detavernier<sup>\*a</sup>

Correction for 'Plasma enhanced atomic layer deposition of  $\text{Ga}_2\text{O}_3$  thin films' by Ranjith K. Ramachandran et al., *J. Mater. Chem. A*, 2014, **2**, 19232–19238.

On the y-axis of Fig. 4, the authors mistyped the unit of thickness as "Å" instead of "nm". This has now been corrected in the new Fig. 4 provided, as shown.

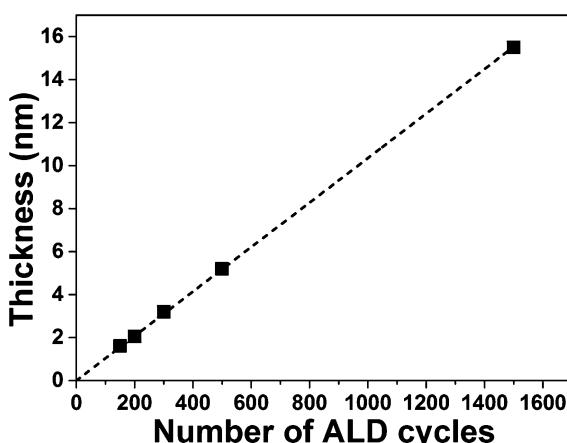


Fig. 4 Thickness of the  $\text{Ga}_2\text{O}_3$  films deposited at 200 °C on  $\text{SiO}_2/\text{Si}$  substrates against the number of ALD cycles.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup>Department of Solid State Sciences, CoCooN, Ghent University, Krijgslaan 281/S1, 9000 Ghent, Belgium. E-mail: Christophe.detavernier@ugent.be; Fax: +32-9-264-4996; Tel: +32-9-264-4354

<sup>b</sup>Department of Solid State Sciences, LumiLab, Ghent University, Krijgslaan 281/S1, 9000 Ghent, Belgium

<sup>c</sup>Centre for Surface Chemistry and Catalysis, Catholic University of Leuven, Kasteelpark Arenberg 23, B-3001 Leuven, Belgium

<sup>d</sup>Laboratory for Chemical Technology, Ghent University, Technologiepark 914, B-9052 Zwijnaarde, Belgium

